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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Data Converters Oscillator Type	A/D 20x8/10b Internal
Data Converters	A/D 20x8/10b
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
EEPROM Size RAM Size	12K x 8
Program Memory Type	FLASH
Program Memory Size	128KB (128K x 8)
Number of I/O	82
Peripherals	DMA, LVD, POR, PWM, WDT
Connectivity	CSI, I ² C, LINbus, UART/USART
Speed	32MHz
Core Size	16-Bit
Core Processor	RL78
Product Status	Obsolete

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

RL78/G13 1. OUTLINE

Table 1-1. List of Ordering Part Numbers

(3/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
			Note	
36 pins	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	Mounted	A G	R5F100CAALA#U0, R5F100CCALA#U0, R5F100CDALA#U0, R5F100CEALA#U0, R5F100CFALA#U0, R5F100CGALA#U0 R5F100CAALA#W0, R5F100CAALA#W0, R5F100CAALA#W0, R5F100CEALA#W0, R5F100CGALA#W0 R5F100CAGLA#W0 R5F100CAGLA#U0, R5F100CAGLA#U0, R5F100CAGLA#U0, R5F100CAGLA#U0 R5F100CAGLA#U0, R5F100CAGLA#W0 R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0
		Not mounted	A	R5F101CAALA#U0, R5F101CCALA#U0, R5F101CDALA#U0, R5F101CEALA#U0, R5F101CFALA#U0, R5F101CGALA#U0 R5F101CAALA#W0, R5F101CCALA#W0, R5F101CDALA#W0,
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	Mounted	A	R5F101CEALA#W0, R5F101CFALA#W0, R5F101CGALA#W0 R5F100EAANA#U0, R5F100ECANA#U0, R5F100EDANA#U0, R5F100EEANA#U0, R5F100EFANA#U0, R5F100EGANA#U0, R5F100EHANA#U0 R5F100EAANA#W0, R5F100ECANA#W0, R5F100EDANA#W0, R5F100EEANA#W0, R5F100EFANA#W0, R5F100EGANA#W0,
			D	R5F100EHANA#W0 R5F100EADNA#U0, R5F100ECDNA#U0, R5F100EDDNA#U0, R5F100EEDNA#U0, R5F100EFDNA#U0, R5F100EGDNA#U0, R5F100EHDNA#U0 R5F100EADNA#W0, R5F100ECDNA#W0, R5F100EDDNA#W0, R5F100EEDNA#W0, R5F100EFDNA#W0, R5F100EGDNA#W0, R5F100EHDNA#W0
			G	R5F100EAGNA#U0, R5F100ECGNA#U0, R5F100EDGNA#U0, R5F100EEGNA#U0, R5F100EFGNA#U0, R5F100EGGNA#U0, R5F100EHGNA#U0 R5F100EAGNA#W0, R5F100ECGNA#W0, R5F100EDGNA#W0, R5F100EEGNA#W0, R5F100EFGNA#W0, R5F100EFGNA#W0, R5F100EHGNA#W0
		Not mounted	A D	R5F101EAANA#U0, R5F101ECANA#U0, R5F101EDANA#U0, R5F101EEANA#U0, R5F101EFANA#U0, R5F101EGANA#U0, R5F101EHANA#U0 R5F101EAANA#W0, R5F101ECANA#W0, R5F101EDANA#W0, R5F101EEANA#W0, R5F101EGANA#W0, R5F101EHANA#W0 R5F101EHANA#W0 R5F101EADNA#U0, R5F101ECDNA#U0, R5F101EDDNA#U0, R5F101EEDNA#U0, R5F101EEDNA#U0, R5F101EEDNA#U0, R5F101EHDNA#U0 R5F101EADNA#W0, R5F101ECDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0,

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

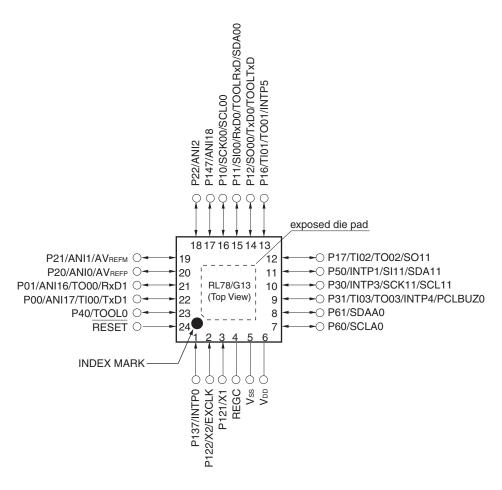
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



RL78/G13 1. OUTLINE

1.3.2 24-pin products

• 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. It is recommended to connect an exposed die pad to $V_{\mbox{\scriptsize ss}}.$

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz

 $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz$ to 16~MHz

LS (low-speed main) mode: 1.8 V \leq V_{DD} \leq 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V \leq V_{DD} \leq 5.5 V@1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fih: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbo	Conditions		HS (high main)		LS (low-sp Mo	,	LV (low-vol		Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SIp setup time (to SCKp↑) Note 1	tsık2	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$ $1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$ $1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		1/fмск+2 0		1/fмск+30		1/fмск+30		ns	
				1/fмск+3 0		1/fмск+30		1/fмск+30		ns	
				1/fмск+4 0		1/fмск+40		1/fмск+40		ns	
		1.6 V ≤	EV _{DD0} ≤ 5.5 V	_		1/fмск+40		1/fмск+40		ns	
SIp hold time (from SCKp↑)	tksi2	1.8 V ≤ E	EV _{DD0} ≤ 5.5 V	1/fмск+3 1		1/fмск+31		1/fмск+31		ns	
Note 2		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		1/fмск+ 250		1/fмск+ 250		1/fмск+ 250		ns	
				_		1/fмск+ 250		1/fмск+ 250		ns	
Delay time from SCKp↓ to	tkso2		C = 30 pF Note 4	$2.7~V \leq EV_{DD0} \leq 5.5$ V		2/f _{MCK+} 44		2/f _{MCK+} 110		2/f _{MCK+} 110	ns
SOp output Note			$2.4~V \le EV_{DD0} \le 5.5$ V		2/fмск+ 75		2/fмск+ 110		2/fмск+ 110	ns	
			$1.8~V \le EV_{DD0} \le 5.5$ V		2/fмск+ 110		2/fмск+ 110		2/fмск+ 110	ns	
			1.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+ 220		2/fмск+ 220		2/fмск+ 220	ns	
			1.6 V ≤ EV _{DD0} ≤ 5.5 V		_		2/fмск+ 220		2/fмск+ 220	ns	

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

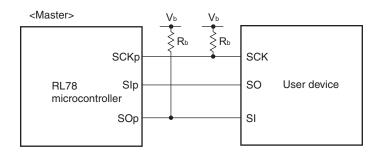
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

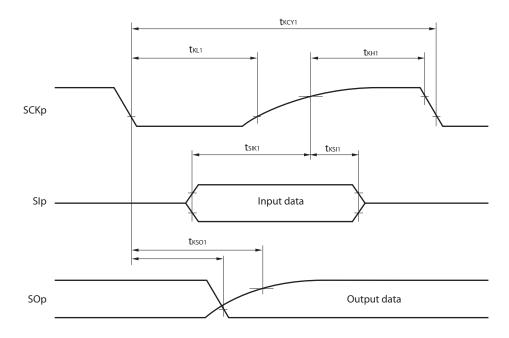
 n: Channel number (mn = 00 to 03, 10 to 13))

CSI mode connection diagram (during communication at different potential)

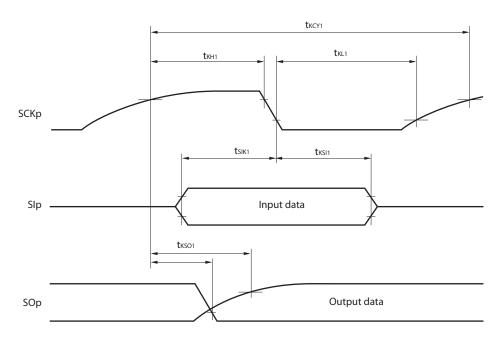


- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number , n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



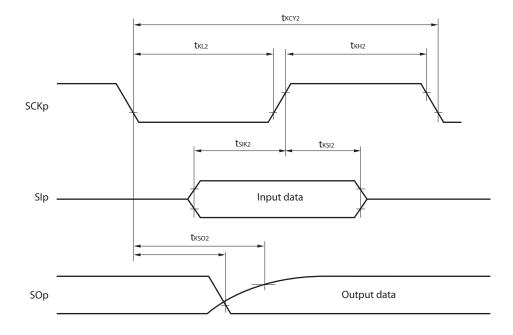
CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



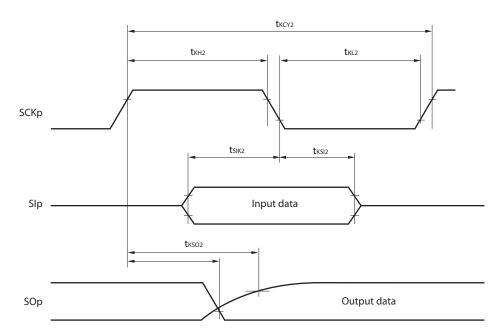
Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



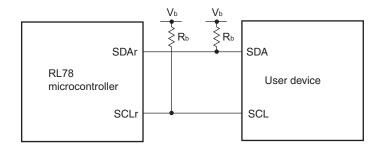
CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



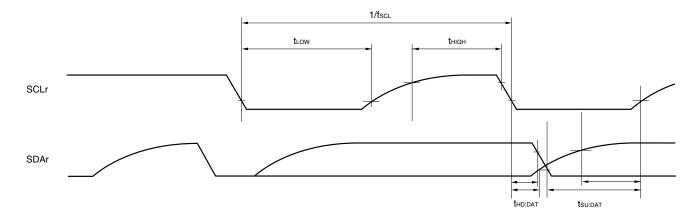
Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remarks 1.** $R_b[\Omega]$:Communication line (SDAr, SCLr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance, $V_b[V]$: Communication line voltage
 - 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00, 01, 02, 10, 12, 13)

2.5.2 Serial interface IICA

(1) I2C standard mode

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	С	Conditions	, ,	h-speed Mode	,	/-speed Mode	,	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	0	100	0	100	0	100	kHz
		mode:	1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
		fc∟k≥ 1 MHz	1.7 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EV _{DD0} ≤ 5.5 V	_	_	0	100	0	100	kHz
Setup time of restart	tsu:sta	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
condition		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	4.7		4.7		μS
Hold time ^{Note 1}	thd:STA	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.7 V ≤ EV _{DD0} :	4.0		4.0		4.0		μS	
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	4.0		4.0		μS
Hold time when SCLA0 =	tLOW	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
" <u>L</u> "		1.8 V ≤ EV _{DD0} :	$1.8~V \leq EV_{DD0} \leq 5.5~V$			4.7		4.7		μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	4.7		4.7		μS
Hold time when SCLA0 =	t HIGH	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
"H"		1.8 V ≤ EV _{DD0} :	4.0		4.0		4.0		μS	
		1.7 V ≤ EV _{DD0} :	4.0		4.0		4.0		μS	
		1.6 V ≤ EV _{DD0} ≤ 5.5 V		_	_	4.0		4.0		μS
Data setup time	tsu:dat	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	250		250		250		ns
(reception)		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	250		250		250		ns
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	250		250		250		ns
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	250		250		ns
Data hold time	thd:dat	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	0	3.45	0	3.45	0	3.45	μS
(transmission) ^{Note 2}		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	0	3.45	0	3.45	0	3.45	μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	0	3.45	0	3.45	0	3.45	μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	0	3.45	0	3.45	μS
Setup time of stop	tsu:sto	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
condition		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V			4.0		4.0		μS
Bus-free time	t BUF	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_		4.7		4.7		μS

(Notes, Caution and Remark are listed on the next page.)



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = V _{BGR}
Input channel	Reference voltage (-) = AVREFM	Reference voltage (-) = Vss	Reference voltage (–) = AVREFM
ANI0 to ANI14	Refer to 2.6.1 (1) .	Refer to 2.6.1 (3) .	Refer to 2.6.1 (4) .
ANI16 to ANI26	Refer to 2.6.1 (2) .		
Internal reference voltage	Refer to 2.6.1 (1) .		_
Temperature sensor output			
voltage			

(1) When reference voltage (+)= AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±3.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2 to ANI14	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μS
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Full-scale error Notes 1, 2	E _{FS}	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±0.25	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±2.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±1.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±2.0	LSB
Analog input voltage	VAIN	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS			V _{BGR} Note 5		V
		Temperature sensor outp (2.4 V \leq VDD \leq 5.5 V, HS	•	\	/TMPS25 Note	5	V

(Notes are listed on the next page.)



LVD Detection Voltage of Interrupt & Reset Mode

(Ta = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conc	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _{LVDA0}	V _{POC2} ,	$V_{POC1}, V_{POC0} = 0, 0, 0$, falling reset voltage	1.60	1.63	1.66	V
mode	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V _{LVDB0}	VPOC2,	VPOC1, VPOC0 = 0, 0, 1	, falling reset voltage	1.80	1.84	1.87	V
	V _{LVDB1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	V _{LVDB2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	V _{LVDB3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	V _{LVDC0}	V _{POC2} ,	VPOC1, VPOC0 = 0, 1, 0	, falling reset voltage	2.40	2.45	2.50	V
	VLVDC1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	V _{LVDD0}	V _{POC2} ,	VPOC1, VPOC0 = 0, 1, 1	, falling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			_	Falling interrupt voltage	2.90	2.96	3.02	V
	V _{LVDD3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V



Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	- 70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	lo _{L2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	TA	In normal operati	on mode programming mode	-40 to +105	°C
	l				

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}. 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}. \text{ Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	EV _{DD0} – 0.7			V
		P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$\label{eq:loss_problem} \begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \\ \text{I}_{\text{OH1}} = -2.0 \ \text{mA} \end{array}$	EV _{DD0} – 0.6			V
			$2.4~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OH1} = -1.5~mA$	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	2.4 V \leq V _{DD} \leq 5.5 V, I _{OH2} = $-100~\mu$ A	V _{DD} – 0.5			V
Output voltage, low	V _{OL1}	P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 8.5~mA$			0.7	V
			$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 3.0~mA$			0.6	V
			$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 1.5~mA$			0.4	V
			$2.4~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 0.6~mA$			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	2.4 V \leq V _{DD} \leq 5.5 V, I _{DL2} = 400 μ A			0.4	V
	Vоьз	P60 to P63	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 15.0~mA$			2.0	V
			$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 5.0~mA$			0.4	V
			$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 3.0~mA$			0.4	V
			$2.4~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 2.0~mA$			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (Ta = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (2/2)

Parameter	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	fih = 32 MHz Note 4	V _{DD} = 5.0 V		0.54	2.90	mA
current	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.54	2.90	mA
				fih = 24 MHz Note 4	V _{DD} = 5.0 V		0.44	2.30	mA
					V _{DD} = 3.0 V		0.44	2.30	mA
				fih = 16 MHz Note 4	V _{DD} = 5.0 V		0.40	1.70	mA
					V _{DD} = 3.0 V		0.40	1.70	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.90	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.45	2.00	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.90	mA
				V _{DD} = 3.0 V	Resonator connection		0.45	2.00	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	1.02	mA
				V _{DD} = 5.0 V	Resonator connection		0.26	1.10	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	1.02	mA
				V _{DD} = 3.0 V	Resonator connection		0.26	1.10	mA
		Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μА	
			clock	T _A = -40°C	Resonator connection		0.44	0.76	μА
			operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	μА
				T _A = +25°C	Resonator connection		0.49	0.76	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.37	1.17	μА
				T _A = +50°C	Resonator connection		0.56	1.36	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.53	1.97	μА
				T _A = +70°C	Resonator connection		0.72	2.16	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.82	3.37	μА
				T _A = +85°C	Resonator connection		1.01	3.56	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		3.01	15.37	μА
				T _A = +105°C	Resonator connection		3.20	15.56	μА
	IDD3 ^{Note 6}	STOP	T _A = -40°C				0.18	0.50	μА
		mode ^{Note 8}	T _A = +25°C				0.23	0.50	μА
			T _A = +50°C				0.30	1.10	μА
			T _A = +70°C				0.46	1.90	μА
			T _A = +85°C				0.75	3.30	μА
			T _A = +105°C				2.94	15.30	μА

(Notes and Remarks are listed on the next page.)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Condit	ions	HS (high-spee	ed main) Mode	Unit
					MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$			Note 1	bps
			$V,$ $2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.6 Note 2	Mbps
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0$			Note 3	bps
			$V,$ $2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$		1.2 Note 4	Mbps
			2.4 V ≤ EV _{DD0} < 3.3			Note 5	bps
			$V,$ $1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 V$		0.43 Note 6	Mbps

Notes 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV_{DD0} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DDO} < 4.0 V and 2.4 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	C	Conditions	HS (high-spe	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tkCY2	$4.0~V \leq EV_{DD0} \leq 5.5$	24 MHz < fмск	28/fмск		ns
		V,	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	8 MHz < fмcк ≤ 20 MHz	20/fмск		ns
			4 MHz < fmck ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		$2.7 \text{ V} \le EV_{DD0} < 4.0$	24 MHz < fмск	40/fмск		ns
		V,	$20~\text{MHz} < \text{fmck} \le 24~\text{MHz}$	32/fмск		ns
		$2.3~V \leq V_b \leq 2.7~V$	16 MHz < fмcк ≤ 20 MHz	28/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	24/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
			24 MHz < fмск	96/fмск		ns
		V,	20 MHz < fмcк ≤ 24 MHz	72/fмск		ns
		$1.6 \ V \leq V_b \leq 2.0 \ V$	16 MHz < fмcк ≤ 20 MHz	64/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	52/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	32/fмск		ns
			fмcк ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level width	tкн2, tкL2	$4.0 \ V \le EV_{DD0} \le 5.$ $2.7 \ V \le V_b \le 4.0 \ V$	$\begin{split} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{split}$			ns
		$ 2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V} $		tkcy2/2 - 36		ns
		$2.4 \ V \le EV_{DD0} < 3.$ $1.6 \ V \le V_b \le 2.0 \ V$		tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) Note2	tsık2	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 $ $ 2.7 \ V \leq V_b \leq 4.0 \ V $	5 V,	1/fмск + 40		ns
		$2.7 \ V \le EV_{DD0} < 4.$ $2.3 \ V \le V_b \le 2.7 \ V$	0 V,	1/fмск + 40		ns
		$2.4 \ V \le EV_{DD0} < 3.$ $1.6 \ V \le V_b \le 2.0 \ V$	3 V,	1/fмск + 60		ns
Slp hold time (from SCKp [↑]) Note 3	tksi2			1/fmck + 62		ns
Delay time from SCKp↓ to SOp output Note 4	tkso2	$4.0~V \leq EV_{DD0} \leq 5.$ $C_b = 30~pF,~R_b = 1$	5 V, 2.7 V \leq V _b \leq 4.0 V, .4 k Ω		2/fмск + 240	ns
to cop output		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2$	0 V, 2.3 V \leq V _b \leq 2.7 V, .7 kΩ		2/fмск + 428	ns
		$2.4 \ V \le EV_{DD0} < 3.$ $C_b = 30 \ pF, \ R_b = 5$	3 V, 1.6 V ≤ V _b ≤ 2.0 V .5 kΩ		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the next page.)

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{\text{BGR}}^{\text{Note 3}}, \text{Reference voltage (-)} = \text{AV}_{\text{REFM}}^{\text{Note 4}} = 0 \text{ V}, \text{HS (high-speed main) mode)}$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	Vain			0		V _{BGR} Note 3	V

- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.
 - 4. When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.
 Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

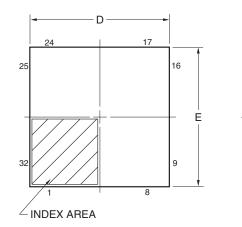
(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

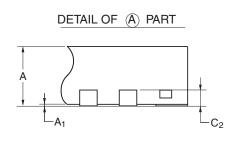
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	nperature sensor output voltage V _{TMPS25} Setting ADS register = 80H, T _A = +25°C			1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	٧
Temperature coefficient	emperature coefficient FVTMPS Temperature sensor that depends on the temperature			-3.6		mV/°C
Operation stabilization wait time	tamp		5			μS

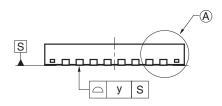
4.5 32-pin Products

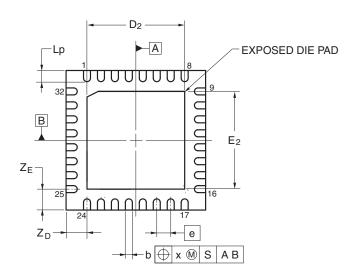
R5F100BAANA, R5F100BCANA, R5F100BDANA, R5F100BEANA, R5F100BFANA, R5F100BGANA R5F101BAANA, R5F101BCANA, R5F101BDANA, R5F101BEANA, R5F101BFANA, R5F101BGANA R5F100BADNA, R5F100BCDNA, R5F100BDDNA, R5F100BEDNA, R5F100BFDNA, R5F100BGDNA R5F101BADNA, R5F101BCDNA, R5F101BDDNA, R5F101BEDNA, R5F100BGGNA, R5F100BGNA, R5F100BGN

JEITA Package code	RENESAS code	Previous code	MASS (TYP.)[g]
P-HWQFN32-5x5-0.50	PWQN0032KB-A	P32K8-50-3B4-5	0.06









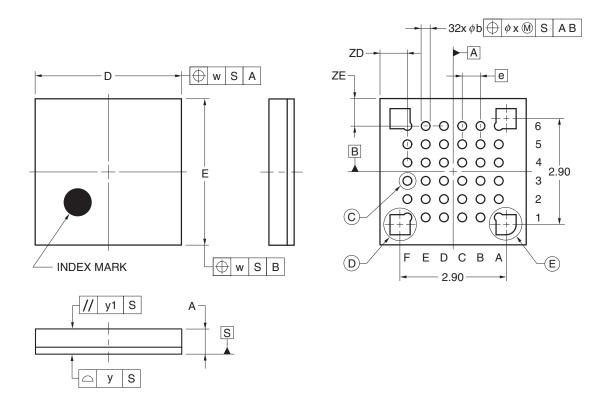
Referance	Dimens	Dimension in Millimeters		
Symbol	Min	Nom	Max	
D	4.95	5.00	5.05	
E	4.95	5.00	5.05	
Α			0.80	
A ₁	0.00			
b	0.18	0.25	0.30	
е		0.50		
Lp	0.30	0.40	0.50	
х			0.05	
у			0.05	
Z _D		0.75		
Z _E		0.75		
C ₂	0.15	0.20	0.25	
D ₂		3.50	_	
E ₂		3.50		

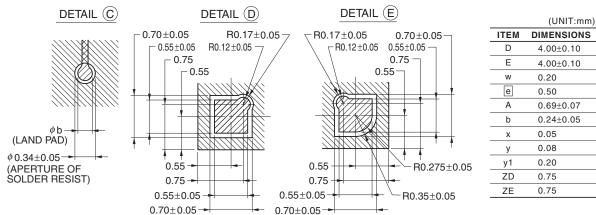
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4.6 36-pin Products

R5F100CAALA, R5F100CCALA, R5F100CDALA, R5F100CEALA, R5F100CFALA, R5F100CGALA R5F101CAALA, R5F101CCALA, R5F101CDALA, R5F101CEALA, R5F101CFALA, R5F101CGALA R5F100CAGLA, R5F100CCGLA, R5F100CDGLA, R5F100CEGLA, R5F100CFGLA, R5F100CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023





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		Description			
Rev.	Date	Page	Summary		
3.00	Aug 02, 2013	81	Modification of figure of AC Timing Test Points		
		81	Modification of description and note 3 in (1) During communication at same potential (UART mode)		
		83	Modification of description in (2) During communication at same potential (CSI mode)		
		84	Modification of description in (3) During communication at same potential (CSI mode)		
		85	Modification of description in (4) During communication at same potential (CSI mode) (1/2)		
		86	Modification of description in (4) During communication at same potential (CSI mode) (2/2)		
		88	Modification of table in (5) During communication at same potential (simplified I ² C mode) (1/2)		
		89	Modification of table and caution in (5) During communication at same potential (simplified I ² C mode) (2/2)		
		91	Modification of table and notes 1 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)		
		92, 93	Modification of table and notes 2 to 7 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)		
		94	Modification of remarks 1 to 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)		
		95	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (1/2)		
		96 Modification of table and caution in (7) Communication at differ (2.5 V, 3 V) (CSI mode) (2/2)			
		97	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)		
		98	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)		
		99	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)		
		100	Modification of remarks 3 and 4 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)		
		102	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)		
		103	Modification of table and caution in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)		
		106	Modification of table in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (1/2)		
		107	Modification of table, note 1, and caution in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)		
		109	Addition of (1) I ² C standard mode		
		111	Addition of (2) I ² C fast mode		
		112	Addition of (3) I ² C fast mode plus		
		112	Modification of IICA serial transfer timing		
		113	Addition of table in 2.6.1 A/D converter characteristics		
		113	Modification of description in 2.6.1 (1)		
		114	Modification of notes 3 to 5 in 2.6.1 (1)		
		115	Modification of description and notes 2, 4, and 5 in 2.6.1 (2)		
		116	Modification of description and notes 3 and 4 in 2.6.1 (3)		
		117	Modification of description and notes 3 and 4 in 2.6.1 (4)		